an electrode of one conductivity type which is formed on said substrate;

an intermediate layer formed on said electrode of the one conductivity type, containing at least one of In, Ag, Ni and Cr;

A1 Cncl.

a reflective layer which is formed on said intermediate layer, contains a metal, and reflects a light;

a light-emitting layer formed on said reflective layer to emit light, having a double-heterostructure in which an active layer is sandwiched between first and second cladding layers; and

a transparent electrode formed on said light-emitting layer to transmit light.

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5. (amended) An element according to claim 1, further comprising a contact layer of the one conductivity type and a strain relaxing layer, formed between said reflective layer and

A2

said light-emitting layer, wherein said strain relaxing layer has a middle band gap between band gaps of said contact layer of the one conductivity type and said first cladding layer.

6. (amended) An element according to claim 1, further comprising a contact layer of an opposite conductivity type formed between said light-emitting layer and said transparent electrode, containing InGaP or InGaAlP.

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17. (amended) A semiconductor light-emitting element comprising:

a transparent semiconductor substrate;

a double-heterostructure which is formed on said semiconductor substrate and contains a

A3

light-emitting layer and first and second cladding layers that sandwich two surfaces of the light-emitting layer;

a contact layer which is formed on said double-heterostructure and has a recessed surface; and

a light-reflecting electrode formed on the recessed surface of said contact layer.

A4

20. (amended) A semiconductor light-emitting diode comprising at least a light-emitting layer formed on a semiconductor substrate,

AP cancel.

wherein a shape of said semiconductor light-emitting element is a polygonal prism having at least five corners or a circular cylinder.

AS

25. (amended) A semiconductor light-emitting element comprising:

a semiconductor substrate;

a light-emitting layer formed on one surface of said semiconductor substrate; and

a photonics crystal layer fused on another surface of said semiconductor substrate,

wherein the other surface of said semiconductor substrate has a rounded edge.